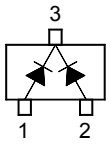
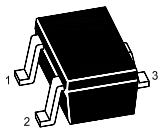
MMBD202CCW

SILICON EPITAXIAL PLANAR SWITCHING DIODE

Application

• Ultra high speed switching





SOT-323 Plastic Package
Marking Code: **PH**

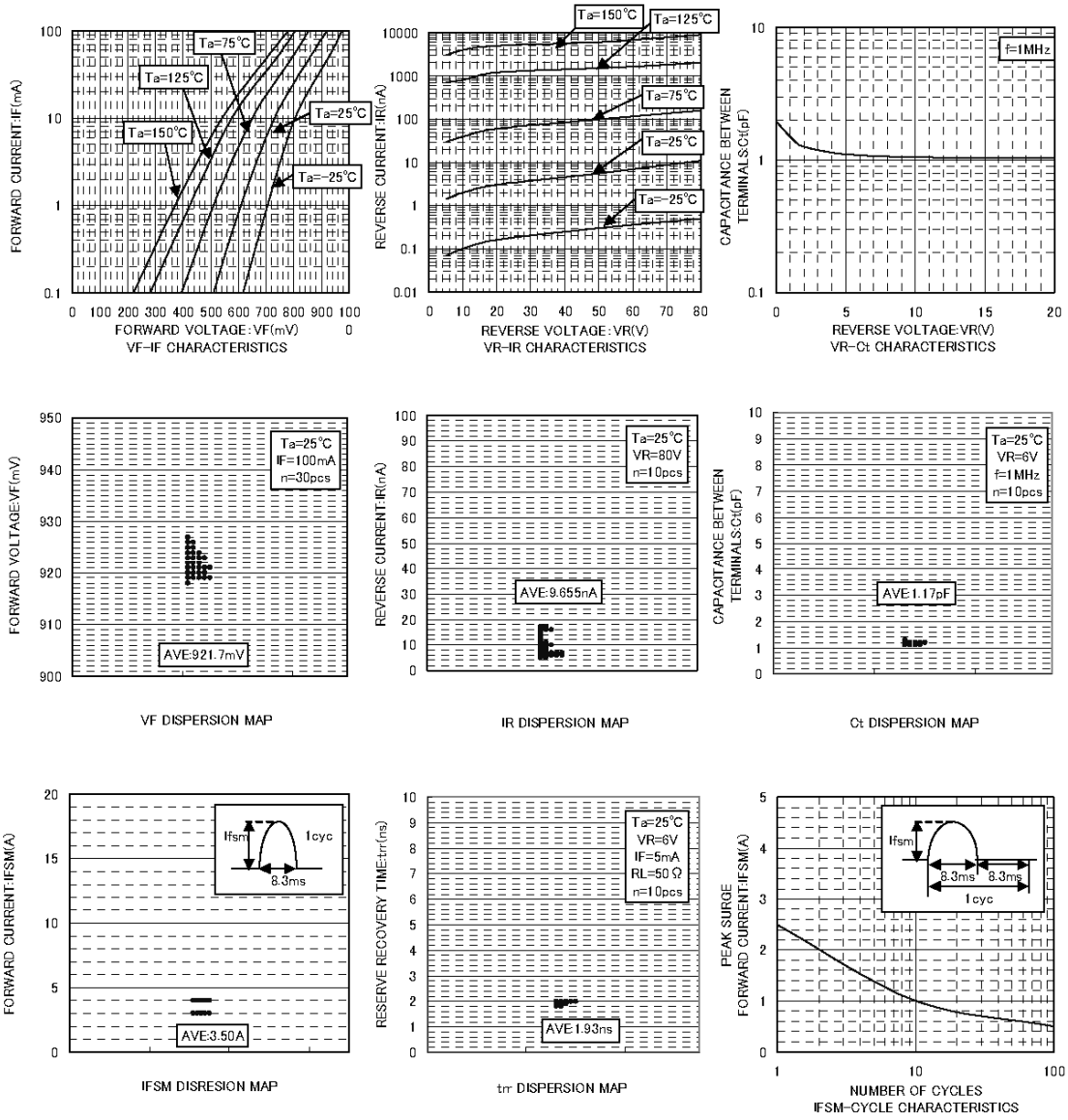
Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	80	V
Reverse Voltage	V_R	80	V
Average Forward Current	I_O	100	mA
Maximum Peak Forward Current	I_{FM}	300	mA
Surge Current (t = 1 μs)	I_{FSM}	4	A
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_s	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 100 mA	V_F	1.2	V
Reverse Current at V_R = 70 V	I_R	0.1	μA
Total Capacitance at V_R = 6 V, f = 1 MHz	C_T	3.5	pF
Reverse Recovery Time at V_R = 6 V, I_F = 5 mA, R_L = 50 Ω	t_{rr}	4	ns

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FORWARD CURRENT:IF(mA)
Ta=75℃
Ta=125℃
Ta=150℃
Ta=25℃
Ta=-25℃
FORWARD VOLTAGE:VF(mV)
VF-IF CHARACTERISTICS
REVERSE CURRENT:IR(nA)
Ta=150℃
Ta=125℃
Ta=75℃
Ta=25℃
Ta=-25℃
REVERSE VOLTAGE:VR(V)
VR-IR CHARACTERISTICS
CAPACITANCE BETWEEN TERMINALS:Ct(pF)
f=1MHz
REVERSE VOLTAGE:VR(V)
VR-Ct CHARACTERISTICS
FORWARD VOLTAGE:VF(mV)
Ta=25℃
IF=100mA
n=30pcs
AVE:921.7mV
VF DISPERSION MAP
REVERSE CURRENT:IR(nA)
Ta=25℃
VR=80V
n=10pcs
AVE:9.655nA
IR DISPERSION MAP
CAPACITANCE BETWEEN TERMINALS:Ct(pF)
Ta=25℃
VR=6V
f=1MHz
n=10pcs
AVE:1.17pF
Ct DISPERSION MAP
PEAK SURGE FORWARD CURRENT:IFSM(A)
Ifsm
1cyc
8.3ms
AVE:3.50A
IFSM DISRESION MAP
RESERVE RECOVERY TIME:trr(ns)
Ta=25℃
VR=6V
IF=5mA
RL=50Ω
n=10pcs
AVE:1.93ns
trr DISPERSION MAP
PEAK SURGE FORWARD CURRENT:IFSM(A)
Ifsm
8.3ms
8.3ms
1cyc
NUMBER OF CYCLES
IFSM-CYCLE CHARACTERISTICS